

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claims 1-7 (canceled).

Claim 8 (currently amended): ~~The duplexer according to Claim 6, wherein a~~  
duplexer, comprising:

a transmission-side band filter including a plurality of surface acoustic wave resonators connected together to define a ladder circuit;

a reception-side band filter including a plurality of surface acoustic wave resonators connected together to define a ladder circuit; wherein

each of the plurality of surface acoustic wave resonators of the transmission-side band filter and the reception-side band filter includes a 47° to 58° rotated, Y-cut, X-propagating LiNbO<sub>3</sub> substrate and an IDT electrode provided on the LiNbO<sub>3</sub> substrate;

the IDT electrode includes a Ti foundation electrode layer disposed on the LiNbO<sub>3</sub> substrate and an Al electrode layer disposed on the Ti foundation electrode layer; and

a (111) face of the Al electrode layer, one of a (001) face and (100) face of the Ti foundation electrode layer, and a (001) face of the LiNbO<sub>3</sub> substrate are aligned in parallel;

where the Ti foundation electrode layer is an epitaxially grown electrode layer on the LiNbO<sub>3</sub> substrate and the Al electrode layer is an epitaxially grown electrode layer on the Ti foundation electrode layer;

in the reception-side band filter, a first inductance is disposed in parallel with respect to at least one serial arm resonator connected to a serial arm of the ladder circuit among the plurality of surface acoustic wave resonators, and in the transmission-

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side band filter, a second inductance is disposed between a parallel arm resonator connected to a parallel arm of the ladder circuit among the plurality of surface acoustic wave resonators and a ground potential; and

the second inductance is defined by a line embedded in the duplexer.

Claim 9 (currently amended): The duplexer according to Claim 8, wherein the first inductance ~~and the second inductance are respectively~~ is defined by ~~at least one of a wire bonding used for electrical connection in the duplexer, a line embedded in the duplexer, and an external coil component.~~

Claim 10 (canceled).

Claim 11 (currently amended): The duplexer according to Claim ~~68~~, wherein the transmission-side band filter includes three serial arm resonators and two parallel arm resonators defining the ladder circuit.

Claim 12 (currently amended): The duplexer according to Claim ~~68~~, wherein the reception-side band filter includes three serial arm resonators and two parallel arm resonators defining the ladder circuit.

Claim 13 (currently amended): The duplexer according to Claim ~~68~~, wherein the LiNbO<sub>3</sub> substrate is a 55° rotated, Y-cut, X-propagating LiNbO<sub>3</sub> substrate.

Claim 14 (currently amended): A communication device, comprising the duplexer according to Claim ~~68~~, wherein the duplexer includes an antenna terminal, an inductance is disposed between the antennal terminal and an antenna, and the duplexer further includes a capacitor connected between a connection point between the inductance and the antenna and a ground potential.

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Claims 15-24 (canceled).

Claim 25 (new): The duplexer according to Claim 8, wherein the transmission-side band filter and the reception-side band filter are mounted by a flip chip bonding method.